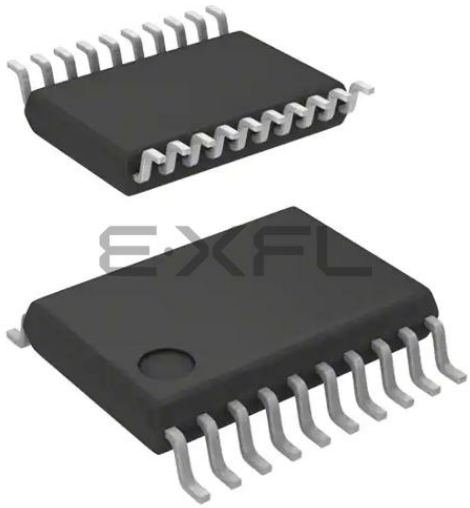
Renesas Electronics America Inc - R5F21324CNSP#W4 Datasheet



Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	15
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21324cnsp-w4

1.2 Product List

Table 1.3 lists Product List for R8C/32C Group, and Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/32C Group.

Table 1.3 Product List for R8C/32C Group **Current of Aug 2010**

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F21321CNSP	4 Kbytes	1 Kbyte × 4	512 bytes	PLSP0020JB-A	N version
R5F21322CNSP	8 Kbytes	1 Kbyte × 4	1 Kbyte	PLSP0020JB-A	
R5F21324CNSP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLSP0020JB-A	
R5F21321CDSP	4 Kbytes	1 Kbyte × 4	512 bytes	PLSP0020JB-A	D version
R5F21322CDSP	8 Kbytes	1 Kbyte × 4	1 Kbyte	PLSP0020JB-A	
R5F21324CDSP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLSP0020JB-A	

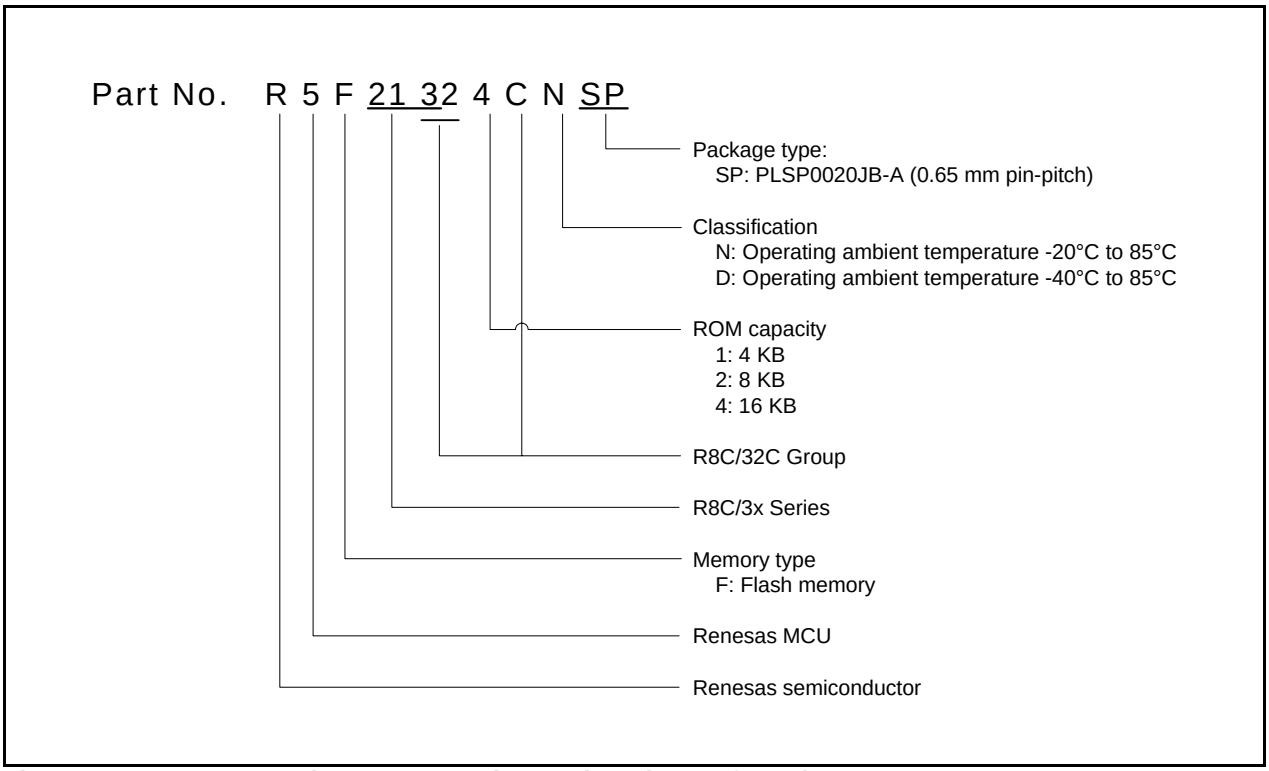


Figure 1.1 Part Number, Memory Size, and Package of R8C/32C Group

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

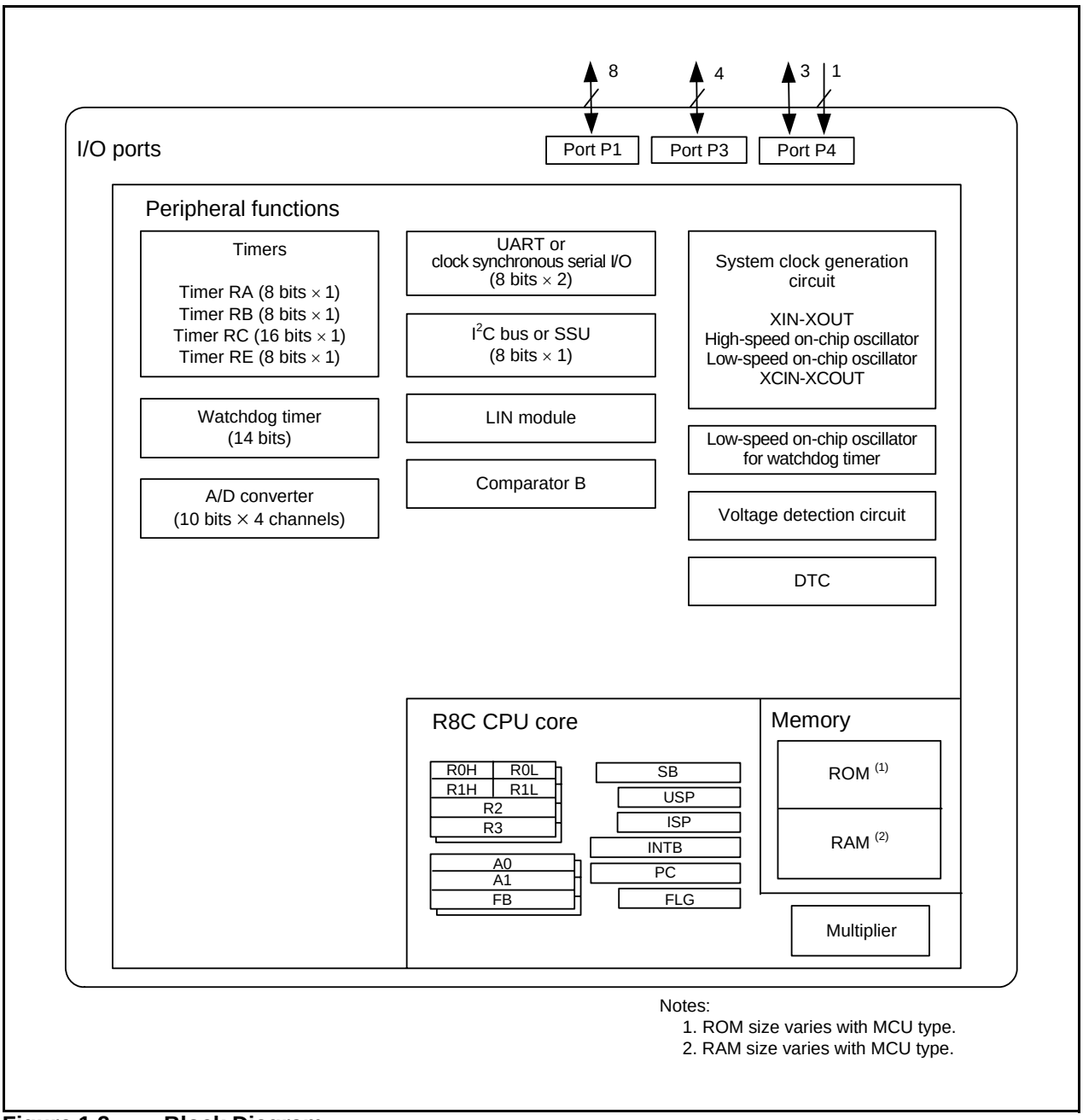


Figure 1.2 Block Diagram

Table 1.4 Pin Name Information by Pin Number

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, Comparator B
1		P4_2						VREF
2	MODE							
3	$\overline{\text{RESET}}$							
4	XOUT(/XCOUT)	P4_7						
5	VSS/AVSS							
6	XIN(/XCIN)	P4_6						
7	VCC/AVCC							
8		P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA	
9		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
10		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3
11		P3_3	$\overline{\text{INT3}}$	(TRCCLK)	($\overline{\text{CTS2}}$/$\overline{\text{RTS2}}$)	$\overline{\text{SCS}}$		IVCMP3
12		P4_5	$\overline{\text{INT0}}$		(RXD2/SCL2)			$\overline{\text{ADTRG}}$
13		P1_7	$\overline{\text{INT1}}$	(TRAIO)				IVCMP1
14		P1_6			(CLK0)			IVREF1
15		P1_5	($\overline{\text{INT1}}$)	(TRAIO)	(RXD0)			
16		P1_4		(TRCCLK)	(TXD0)			
17		P1_3	$\overline{\text{KI3}}$	TRBO (/TRCIOC)				AN11
18		P1_2	$\overline{\text{KI2}}$	(TRCIOB)				AN10
19		P1_1	$\overline{\text{KI1}}$	(TRCIOA/ TRCTRG)				AN9
20		P1_0	$\overline{\text{KI0}}$	(TRCIOD)				AN8

Note:
1. Can be assigned to the pin in parentheses by a program.

Table 4.7 SFR Information (7) (1)

Address	Register	Symbol	After Reset
0180h	Timer RA Pin Select Register	TRASR	00h
0181h	Timer RC Pin Select Register	TRBRCSR	00h
0182h	Timer RC Pin Select Register 0	TRCPSR0	00h
0183h	Timer RC Pin Select Register 1	TRCPSR1	00h
0184h			
0185h			
0186h			
0187h			
0188h	UART0 Pin Select Register	U0SR	00h
0189h			
018Ah	UART2 Pin Select Register 0	U2SR0	00h
018Bh	UART2 Pin Select Register 1	U2SR1	00h
018Ch	SSU / IIC Pin Select Register	SSUIICSR	00h
018Dh			
018Eh	INT Interrupt Input Pin Select Register	INTSR	00h
018Fh	I/O Function Pin Select Register	PINSR	00h
0190h			
0191h			
0192h			
0193h	SS Bit Counter Register	SSBR	11111000b
0194h	SS Transmit Data Register L / IIC bus Transmit Data Register (2)	SSTDR / ICDRT	FFh
0195h	SS Transmit Data Register H (2)	SSTDRH	FFh
0196h	SS Receive Data Register L / IIC bus Receive Data Register (2)	SSRDR / ICDRR	FFh
0197h	SS Receive Data Register H (2)	SSRDRH	FFh
0198h	SS Control Register H / IIC bus Control Register 1 (2)	SSCRH / ICCR1	00h
0199h	SS Control Register L / IIC bus Control Register 2 (2)	SSCRL / ICCR2	01111101b
019Ah	SS Mode Register / IIC bus Mode Register (2)	SSMR / ICMR	00010000b / 00011000b
019Bh	SS Enable Register / IIC bus Interrupt Enable Register (2)	SSER / ICIER	00h
019Ch	SS Status Register / IIC bus Status Register (2)	SSSR / ICSR	00h / 0000X000b
019Dh	SS Mode Register 2 / Slave Address Register (2)	SSMR2 / SAR	00h
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h	Flash Memory Status Register	FST	10000X00b
01B3h			
01B4h	Flash Memory Control Register 0	FMR0	00h
01B5h	Flash Memory Control Register 1	FMR1	00h
01B6h	Flash Memory Control Register 2	FMR2	00h
01B7h			
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

X: Undefined

Notes:
1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.9 SFR Information (9) (1)

Address	Register	Symbol	After Reset
2C00h	DTC Transfer Vector Area		XXh
2C01h	DTC Transfer Vector Area		XXh
2C02h	DTC Transfer Vector Area		XXh
2C03h	DTC Transfer Vector Area		XXh
2C04h	DTC Transfer Vector Area		XXh
2C05h	DTC Transfer Vector Area		XXh
2C06h	DTC Transfer Vector Area		XXh
2C07h	DTC Transfer Vector Area		XXh
2C08h	DTC Transfer Vector Area		XXh
2C09h	DTC Transfer Vector Area		XXh
2C0Ah	DTC Transfer Vector Area		XXh
:	DTC Transfer Vector Area		XXh
:	DTC Transfer Vector Area		XXh
2C3Ah	DTC Transfer Vector Area		XXh
2C3Bh	DTC Transfer Vector Area		XXh
2C3Ch	DTC Transfer Vector Area		XXh
2C3Dh	DTC Transfer Vector Area		XXh
2C3Eh	DTC Transfer Vector Area		XXh
2C3Fh	DTC Transfer Vector Area		XXh
2C40h	DTC Control Data 0	DTCD0	XXh
2C41h			XXh
2C42h			XXh
2C43h			XXh
2C44h			XXh
2C45h			XXh
2C46h			XXh
2C47h			XXh
2C48h	DTC Control Data 1	DTCD1	XXh
2C49h			XXh
2C4Ah			XXh
2C4Bh			XXh
2C4Ch			XXh
2C4Dh			XXh
2C4Eh			XXh
2C4Fh			XXh
2C50h	DTC Control Data 2	DTCD2	XXh
2C51h			XXh
2C52h			XXh
2C53h			XXh
2C54h			XXh
2C55h			XXh
2C56h			XXh
2C57h			XXh
2C58h	DTC Control Data 3	DTCD3	XXh
2C59h			XXh
2C5Ah			XXh
2C5Bh			XXh
2C5Ch			XXh
2C5Dh			XXh
2C5Eh			XXh
2C5Fh			XXh
2C60h	DTC Control Data 4	DTCD4	XXh
2C61h			XXh
2C62h			XXh
2C63h			XXh
2C64h			XXh
2C65h			XXh
2C66h			XXh
2C67h			XXh
2C68h	DTC Control Data 5	DTCD5	XXh
2C69h			XXh
2C6Ah			XXh
2C6Bh			XXh
2C6Ch			XXh
2C6Dh			XXh
2C6Eh			XXh
2C6Fh			XXh

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.10 SFR Information (10) (1)

Address	Register	Symbol	After Reset
2C70h	DTC Control Data 6	DTCD6	XXh
2C71h			XXh
2C72h			XXh
2C73h			XXh
2C74h			XXh
2C75h			XXh
2C76h			XXh
2C77h			XXh
2C78h	DTC Control Data 7	DTCD7	XXh
2C79h			XXh
2C7Ah			XXh
2C7Bh			XXh
2C7Ch			XXh
2C7Dh			XXh
2C7Eh			XXh
2C7Fh			XXh
2C80h	DTC Control Data 8	DTCD8	XXh
2C81h			XXh
2C82h			XXh
2C83h			XXh
2C84h			XXh
2C85h			XXh
2C86h			XXh
2C87h			XXh
2C88h	DTC Control Data 9	DTCD9	XXh
2C89h			XXh
2C8Ah			XXh
2C8Bh			XXh
2C8Ch			XXh
2C8Dh			XXh
2C8Eh			XXh
2C8Fh			XXh
2C90h	DTC Control Data 10	DTCD10	XXh
2C91h			XXh
2C92h			XXh
2C93h			XXh
2C94h			XXh
2C95h			XXh
2C96h			XXh
2C97h			XXh
2C98h	DTC Control Data 11	DTCD11	XXh
2C99h			XXh
2C9Ah			XXh
2C9Bh			XXh
2C9Ch			XXh
2C9Dh			XXh
2C9Eh			XXh
2C9Fh			XXh
2CA0h	DTC Control Data 12	DTCD12	XXh
2CA1h			XXh
2CA2h			XXh
2CA3h			XXh
2CA4h			XXh
2CA5h			XXh
2CA6h			XXh
2CA7h			XXh
2CA8h	DTC Control Data 13	DTCD13	XXh
2CA9h			XXh
2CAAh			XXh
2CABh			XXh
2CACh			XXh
2CADh			XXh
2CAEh			XXh
2CAFh			XXh

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

Table 5.5 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		1,000 (3)	–	–	times
–	Byte program time		–	80	500	µs
–	Block erase time		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5 + CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time (7)	Ambient temperature = 55°C	20	–	–	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.6 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		10,000 (3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	160	1,500	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	300	1,500	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	1	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5 + CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 (7)	–	85	°C
–	Data hold time (8)	Ambient temperature = 55 °C	20	–	–	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40°C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

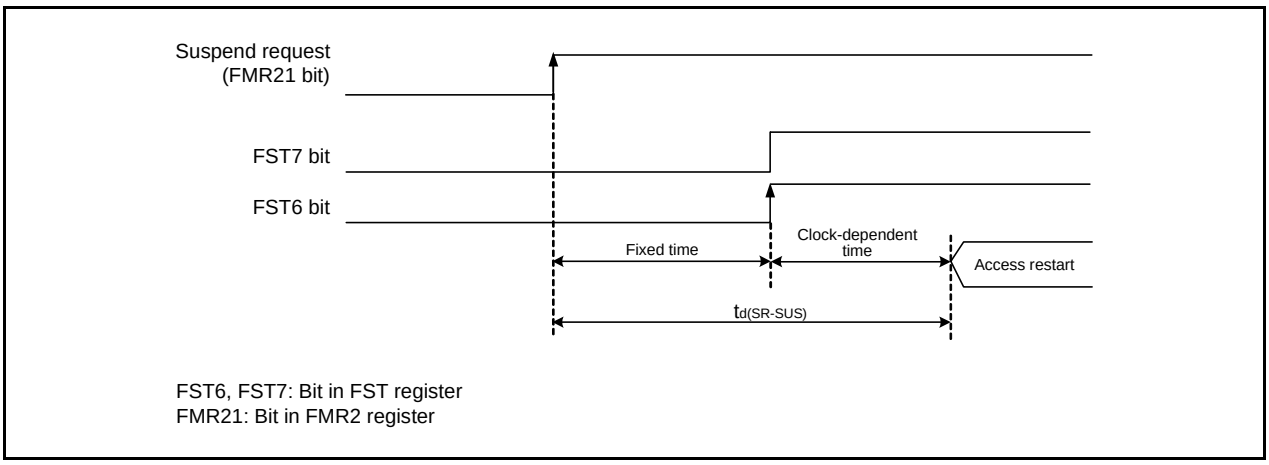


Figure 5.2 Time delay until Suspend

Table 5.7 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
–	Voltage detection 0 circuit response time (4)	At the falling of Vcc from 5 V to (Vdet0_0 – 0.1) V	–	6	150	µs
–	Voltage detection circuit self power consumption	VCA25 = 1, Vcc = 5.0 V	–	1.5	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		–	–	100	µs

Notes:
1. The measurement condition is Vcc = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.8 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of Vcc	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of Vcc	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of Vcc	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of Vcc	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of Vcc	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of Vcc	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of Vcc	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of Vcc	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of Vcc	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of Vcc	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of Vcc	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of Vcc	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of Vcc	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of Vcc	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of Vcc	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of Vcc	4.20	4.45	4.75	V
–	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	–	0.07	–	V
		Vdet1_6 to Vdet1_F selected	–	0.10	–	V
–	Voltage detection 1 circuit response time (3)	At the falling of Vcc from 5 V to (Vdet1_0 – 0.1) V	–	60	150	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, Vcc = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		–	–	100	µs

Notes:
1. The measurement condition is Vcc = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.9 Voltage Detection 2 Circuit Electrical Characteristics

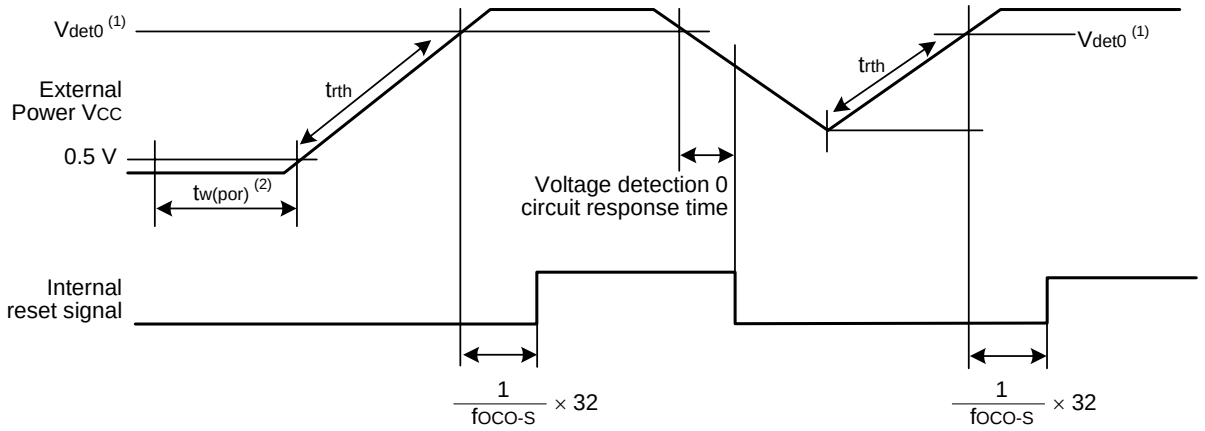
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0	At the falling of V_{CC}	3.70	4.00	4.30	V
–	Hysteresis width at the rising of Vcc in voltage detection 2 circuit		–	0.10	–	V
–	Voltage detection 2 circuit response time (2)	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	20	150	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.10 Power-on Reset Circuit (2)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{rth}	External power V_{CC} rise gradient	(1)	0	–	50,000	mV/msec

Notes:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



Notes:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of User's Manual: Hardware (REJ09B0573) for details.
2. $t_{w(por)}$ indicates the duration the external power V_{CC} must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain $t_{w(por)}$ for 1 ms or more.

Figure 5.3 Power-on Reset Circuit Electrical Characteristics

Table 5.14 Timing Requirements of Synchronous Serial Communication Unit (SSU) (1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC} (2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC} (2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC} (2)
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	$1.5t_{CYC}$ + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	$1.5t_{CYC}$ + 200	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

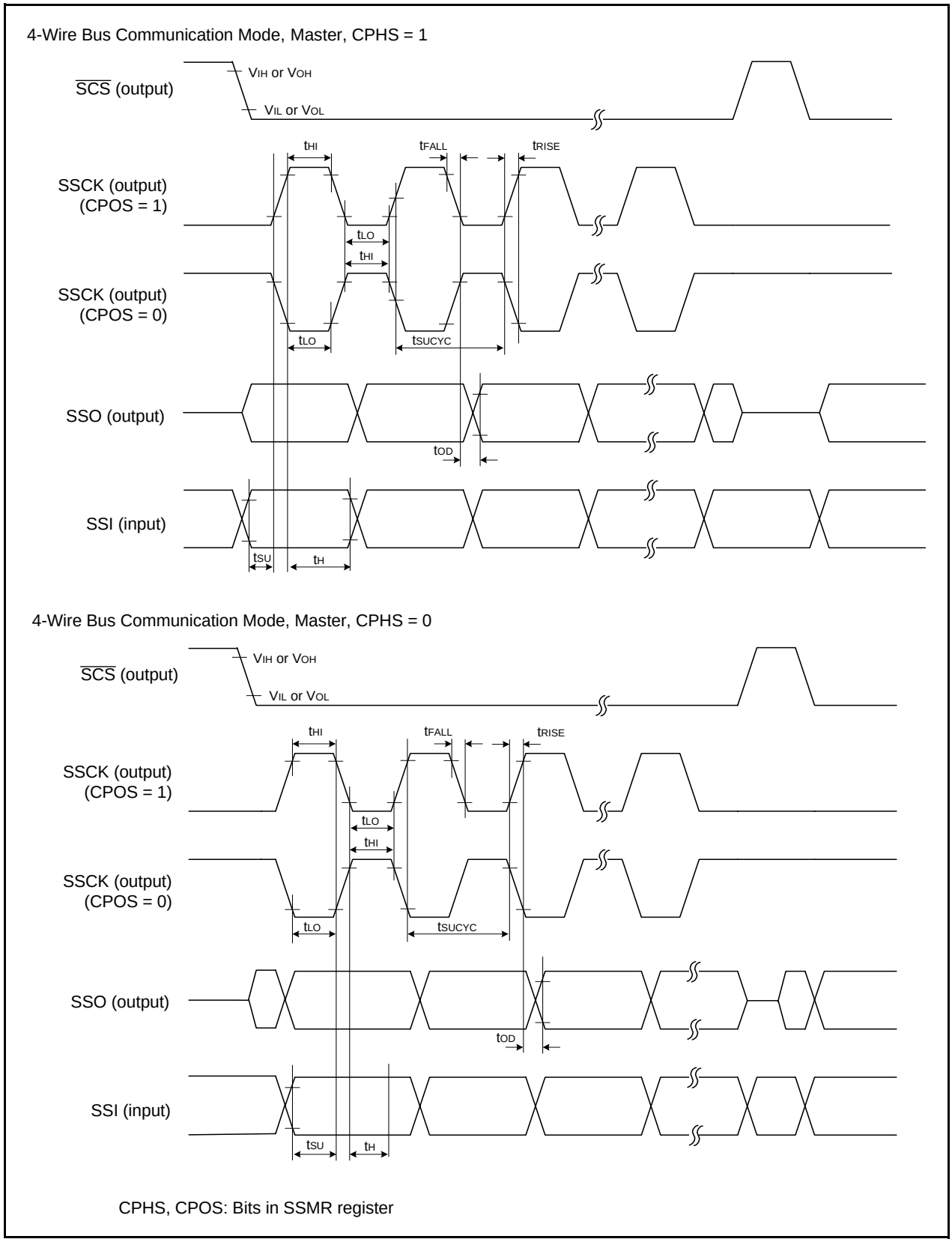


Figure 5.4 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)

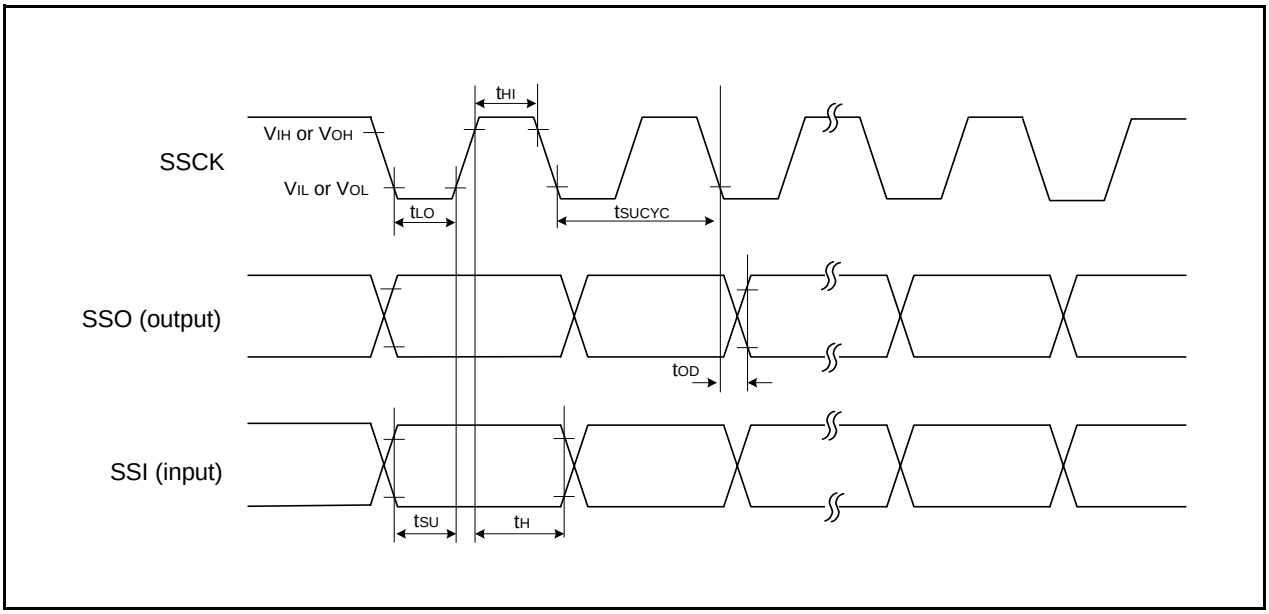


Figure 5.6 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

Table 5.20 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width	100	–	ns
$t_{W(CKL)}$	CLKi input “L” width	100	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	50	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0, 2

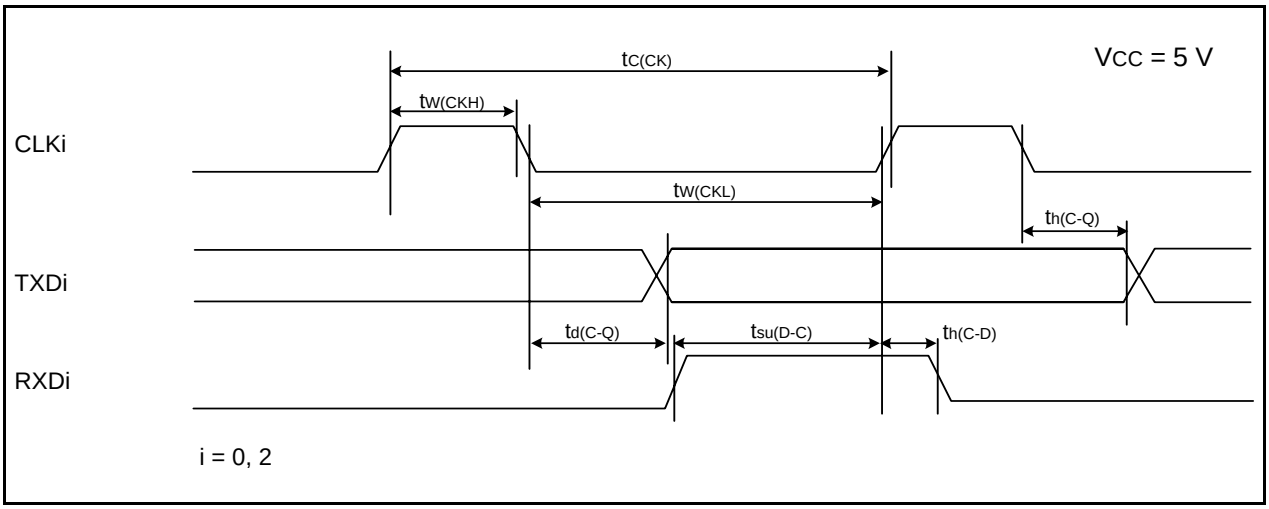


Figure 5.10 Serial Interface Timing Diagram when VCC = 5 V

Table 5.21 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	250 (1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	250 (2)	–	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

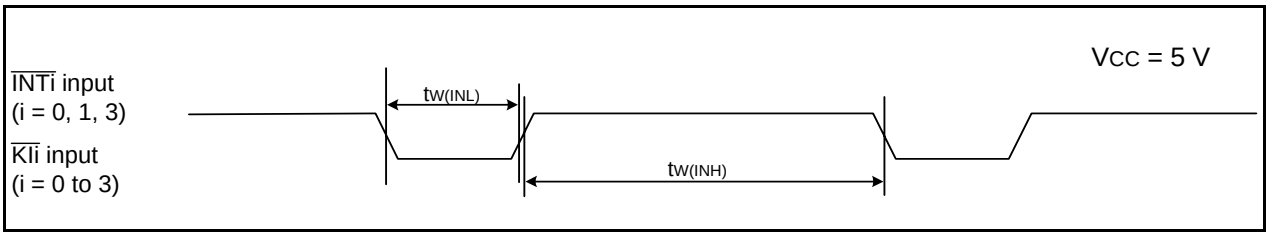


Figure 5.11 Input Timing Diagram for External Interrupt INTi and Key Input Interrupt KIi when Vcc = 5 V

Table 5.23 Electrical Characteristics (4) [2.7 V ≤ Vcc < 3.3 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	10	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	7.5	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	390	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	80	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Table 5.26 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	–	ns
$t_{W(CKH)}$	CLKi input “H” width	150	–	ns
$t_{W(CKL)}$	CLKi Input “L” width	150	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	70	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0, 2

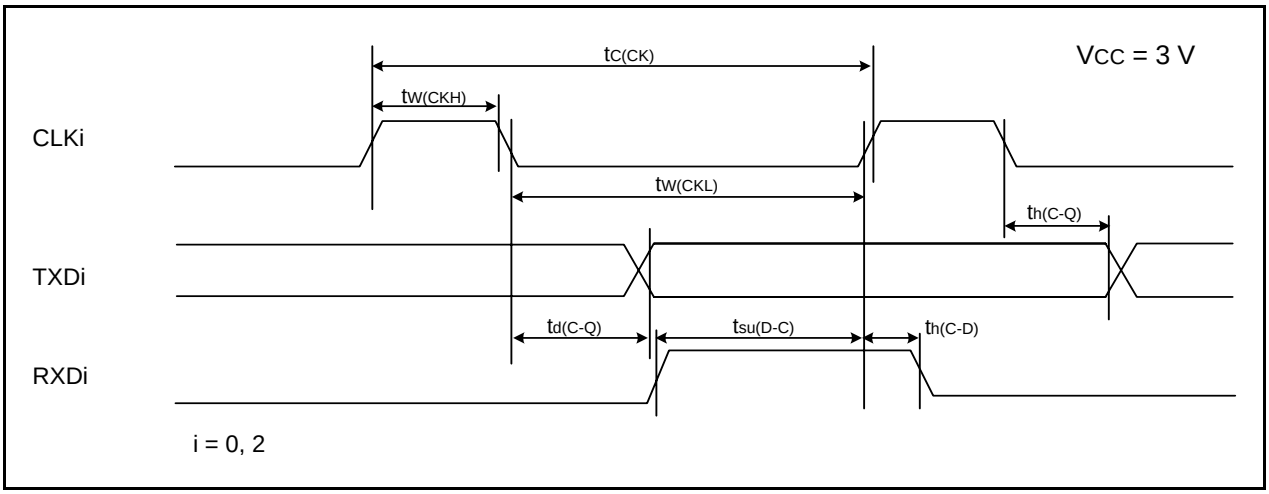


Figure 5.14 Serial Interface Timing Diagram when VCC = 3 V

Table 5.27 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	380 (1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	380 (2)	–	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

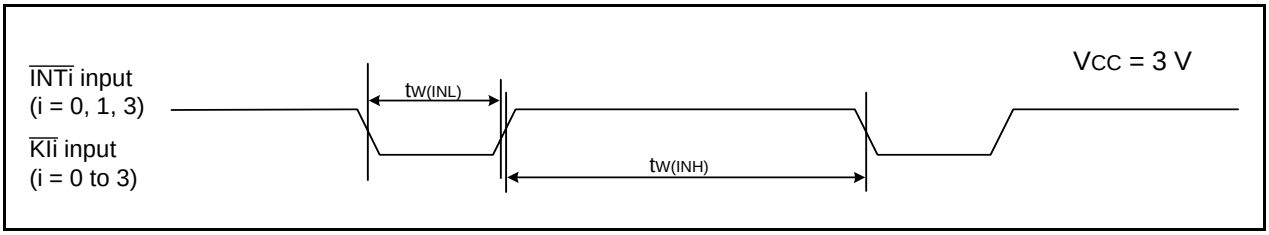


Figure 5.15 Input Timing Diagram for External Interrupt INTi and Key Input Interrupt KIi when Vcc = 3 V

Table 5.29 Electrical Characteristics (6) [1.8 V ≤ Vcc < 2.7 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 1.8 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	2.2	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	0.8	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	2.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.7	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	80	350	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Timing requirements
(Unless Otherwise Specified: V_{CC} = 2.2 V, V_{SS} = 0 V at Topr = 25°C)

Table 5.30 External Clock Input (XOUT, XCIN)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	200	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	90	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	90	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

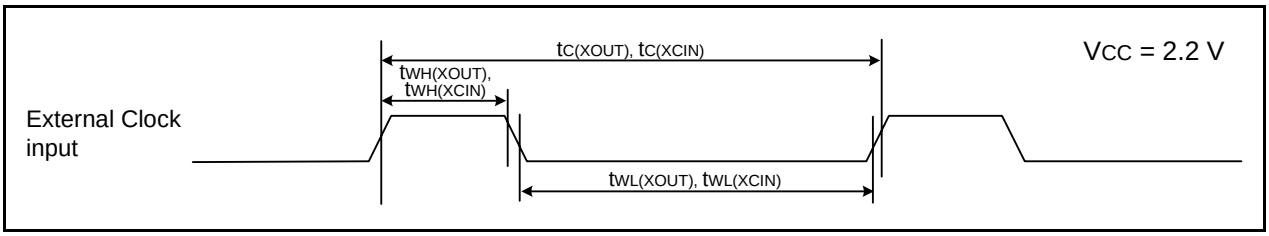


Figure 5.16 External Clock Input Timing Diagram when V_{CC} = 2.2 V

Table 5.31 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	500	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	200	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	200	–	ns

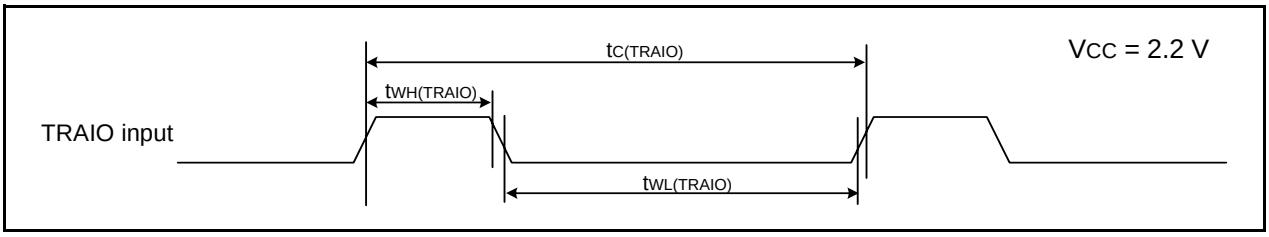


Figure 5.17 TRAIO Input Timing Diagram when V_{CC} = 2.2 V

General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

   Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

   — The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

2. Processing at Power-on

   The state of the product is undefined at the moment when power is supplied.

   — The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.

   In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

   In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

3. Prohibition of Access to Reserved Addresses

   Access to reserved addresses is prohibited.

   — The reserved addresses are provided for the possible future expansion of functions. Do not access these addresses; the correct operation of LSI is not guaranteed if they are accessed.

4. Clock Signals

   After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

   — When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.

5. Differences between Products

   Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

   — The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.

Notice

1. All information included in this document is current as of the date this document is issued. Such information, however, is subject to change without any prior notice. Before purchasing or using any Renesas Electronics products listed herein, please confirm the latest product information with a Renesas Electronics sales office. Also, please pay regular and careful attention to additional and different information to be disclosed by Renesas Electronics such as that disclosed through our website.
2. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
3. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part.
4. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
5. When exporting the products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations. You should not use Renesas Electronics products or the technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations.
6. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
7. Renesas Electronics products are classified according to the following three quality grades: "Standard", "High Quality", and "Specific". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below. You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application categorized as "Specific" without the prior written consent of Renesas Electronics. Further, you may not use any Renesas Electronics product for any application for which it is not intended without the prior written consent of Renesas Electronics. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for an application categorized as "Specific" or for which the product is not intended where you have failed to obtain the prior written consent of Renesas Electronics. The quality grade of each Renesas Electronics product is "Standard" unless otherwise expressly specified in a Renesas Electronics data sheets or data books, etc.
   - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots.
   - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; safety equipment; and medical equipment not specifically designed for life support.
   - "Specific": Aircraft; aerospace equipment; submersible repeaters; nuclear reactor control systems; medical equipment or systems for life support (e.g. artificial life support devices or systems), surgical implantations, or healthcare intervention (e.g. excision, etc.), and any other applications or purposes that pose a direct threat to human life.
8. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
9. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or system manufactured by you.
10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
11. This document may not be reproduced or duplicated, in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.

(Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

(Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

RENESAS

SALES OFFICES Renesas Electronics Corporation http://www.renesas.com

Refer to "http://www.renesas.com/" for the latest and detailed information.

Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
7F, No. 363 Fu Shing North Road Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
1 harbourFront Avenue, #06-10, keppel Bay Tower, Singapore 098632
Tel: +65-6213-0200, Fax: +65-6278-8001

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141

Colophon 1.0